

### REMARKS

Claims 1, 2, 6, 7, 11-16, 27-38, 46 and 55-63 are currently pending in the application, with claims 1, 11 and 55 being independent. Claims 3-5, 8-10, 17-26, 39-45, 47-54 and 64-68 have been canceled.

Applicant acknowledges with appreciation the Examiner's allowance of claims 1, 2, 6, 7, 12-16, 38 and 46. However, in response to the Examiner's statement of reasons for allowance, applicant notes that claim 1 recites "introducing ions of a p-type impurity into *at least* a portion of *only* said first semiconductor island without mass separation" (emphasis added), while the statement of reasons for allowance indicates that the prior art does not show "introducing p-type impurities into *only* a portion of the semiconductor island without mass separation" (emphasis added). Applicant assumes that this difference results from a typographical error and that the Examiner intended to acknowledge that the prior art does not describe or suggest "introducing ions of a p-type impurity into at least a portion of only said first semiconductor island without mass separation," as recited in claim 1.

As requested by the Examiner, withdrawn claims 3-5, 8-10, 17-26, 39-45, 47-54 and 64-68 have been canceled. However, withdrawn claim 11 and its dependent claims 27-37 have not been canceled in view of the indication in the restriction requirement dated May 30, 2002, that claim 11 is generic to the elected species. Applicant also notes that claim 11, similarly to claim 1, recites "introducing ions of an impurity comprising boron into at least a portion of said semiconductor island without mass separation, wherein said portion is to become a channel region of a thin film transistor" and that boron is a p-type impurity. For these reasons, applicant submits that claims 11 and 27-37 also should be allowed.

Applicant has also refrained from canceling independent claim 55 and its dependent claims 56-63. Similarly to claim 1, independent claim 55 recites "introducing ions of a p-type impurity into at least a portion of only said first semiconductor island by plasma doping without mass separation wherein said portion is to become a channel region of a thin film transistor".

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Accordingly, since claim 55 also recites the allowable subject matter of claim 1, applicant submits that claims 55-63 also should be allowed.

Applicant submits that all claims are in condition for allowance.

No fees are believed to be due. Please apply any charges or credits to deposit account 06-1050.

Respectfully submitted,

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